

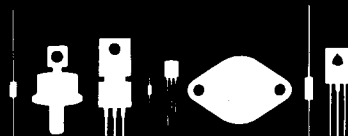
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145 Adams Avenue
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SE9300
SE9301
SE9302

Silicon NPN Transistor

Darlington Power

JEDEC TO-220 Case

DESCRIPTION

The CENTRAL SEMICONDUCTOR SE9300, 01, 02 are Silicon NPN Epitaxial Base, Monolithic Diffused Resistor Type Darlington Construction Power Transistors designed for audio amplifiers and medium power linear and switching applications.

MAXIMUM RATINGS ($T_C=25^{\circ}C$)

		9300	9301	9302
Collector to Emitter Voltage	V _{CEO}	60V	80V	100V
Collector to Base Voltage	V _{CBO}	60V	80V	100V
Emitter to Base Voltage	V _{EBO}	5V	5V	5V
Collector Current	I _C	10A	10A	10A
Power Dissipation	P _D	70W	70W	70W
Operating Junction Temperature	T _J	-65 to +150°C		
Storage Temperature	T _{stg}	-65 to +150°C		

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}C$)

Symbol	Test Conditions	Min.	Max.	Unit
I _{CBO}	V _{CE} =Rated V _{CEO}		200	uA
I _{EBO}	V _{EB} =5.0V		4.0	mA
I _{CEO}	V _{CE} =0.5xRated V _{CEO}		500	uA
V _{CEO}	I _C =100mA	9300 60 9301 80 9302 100		V
V _{CE(S)}	I _C =4.0A, I _B =16mA		2.0	V
V _{CE(S)}	I _C =7.5A, I _B =150mA		2.5	V
V _{BE(ON)}	V _{CE} =3.0V, I _C =4.0A		2.5	V
V _{BE(ON)}	V _{CE} =3.0V, I _C =7.5A		3.0	V
h _{FE}	V _{CE} =3.0V, I _C =1.0A	750		-
h _{FE}	V _{CE} =3.0V, I _C =4.0A	1,000		-
h _{FE}	V _{CE} =3.0V, I _C =7.5A	100		-
h _{fe}	V _{CE} =3.0V, I _C =4.0A, f=1.0 MHz	1.0		-



To-220